

Please enter the following amended claims 1, 6, 7, 8 and 9 as follows:

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1. (Amended) A lithographic projection apparatus comprising:

a radiation system to supply a projection beam of radiation;

a support structure to support patterning structure, the patterning structure serving to pattern the projection beam according to a desired pattern;

a substrate table to hold a substrate; and

a projection system to project the patterned beam onto a target of the substrate, wherein a space containing at least part of said projection system is at a pressure of about 0.1 to 10 Pa and contains argon, nitrogen, helium or a mixture thereof.

6. (Amended) An apparatus according to claim 1, wherein the pressure in said space is from 1 to 5 Pa.

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7. (Amended) An apparatus according to claim 6, wherein the pressure in said space is from 2 to 3 Pa.

8. (Amended) A method of manufacturing a device using a lithographic projection apparatus comprising:

projecting a patterned beam of radiation onto a target portion of a layer of radiation-sensitive material on a substrate; and

supplying a continuous flow of argon, nitrogen, helium or a mixture thereof to a space containing at least a part of said projection system, wherein the pressure in said space is from 0.1 to 10 Pa.

9. (Amended) A semiconductor device manufactured in accordance with a method comprising:

projecting a patterned beam of radiation onto a target portion of radiation-sensitive material on a substrate; and

supplying a continuous flow of argon, nitrogen, helium or a mixture thereof to a space containing at least a part of said projection system, wherein the pressure in said space is from 0.1 to 10 Pa.

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[Please add new claims 10-16 as follows:]

10. (New) An apparatus according to claim 1, further comprising an illumination system wherein a space containing at least part of said illumination system is at a pressure of about 0.1 to 10 Pa and contains argon, nitrogen, helium or a mixture thereof.

11. (New) An apparatus according to claim 1, wherein the space containing the part of the projection system is supplied with a continuous flow of argon, nitrogen, helium or a mixture thereof.

12. (New) An apparatus according to claim 11, wherein the pressure in the space containing the part of the projection system is from 1 to 5 Pa.

13. (New) An apparatus according to claim 12, wherein the pressure in the space containing the part of the projection system is from 2 to 3 Pa.

14. (New) An apparatus according to claim 10, wherein the space containing the part of the illumination space is supplied with a continuous flow of argon, nitrogen, helium or a mixture thereof.

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15. (New) An apparatus according to claim 14, wherein the pressure in the space containing the part of the illumination system is from 1 to 5 Pa.

16. (New) An apparatus according to claim 15, wherein the pressure in the space containing the part of the illumination system is from 2 to 3 Pa.

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**See the attached Appendix for the changes made to effect the above amended  
paragraphs of the specification and amended claims**